NSN 5962-01-248-8654

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View Online at https://aerobasegroup.com/nsn/5962-01-248-8654

Body Length:

1.060 inches

Body Width:

Between 0.220 inches and 0.310 inches

Body Height:

0.185 inches

Maximum Power Dissipation Rating:

2.0 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

Features Provided:

Hermetically sealed and burn in and programmable and bipolar and monolithic

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Bipolar metal-oxide semiconductor

Input Circuit Pattern:

12 input

Case Outline Source And Designator:

D-8 mil-m-38510

Current Rating Per Characteristic:

100.00 milliamperes output sink

Terminal Surface Treatment:

Solder

Voltage Rating And Type Per Characteristic:

5.0 volts power source

Time Rating Per Chacteristic:

45.00 nanoseconds propagation delay time, low to high level output and 45.00 nanoseconds propagation delay time, high to low level output

Memory Device Type:

Pal

Test Data Document:

81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

20 printed circuit

Specification Data:

81349-mil-m-38510/503 government specification

Shelf Life:

NI/o

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Demilitarization:

No

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